74HC165-Q100; 74HCT165-Q100

8-bit parallel-in/serial out shift register

Rev. 1 — 17 July 2012 **Product data sheet**

1. General description

The 74HC165-Q100; 74HCT165-Q100 are high-speed Si-gate CMOS devices that comply with JEDEC standard no. 7A. They are pin compatible with Low-power Schottky TTL (LSTTL).

The 74HC165-Q100; 74HCT165-Q100 are 8-bit parallel-load or serial-in shift registers with complementary serial outputs (Q7 and $\overline{\text{Q7}}$) available from the last stage. When the parallel load ($\overline{\text{PL}}$) input is LOW, parallel data from the D0 to D7 inputs are loaded into the register asynchronously.

When $\overline{\text{PL}}$ is HIGH, data enters the register serially at the DS input and shifts one place to the right (Q0 → Q1 → Q2, etc.) with each positive-going clock transition. This feature allows parallel-to-serial converter expansion by tying the Q7 output to the DS input of the succeeding stage.

The clock input is a gated-OR structure which allows one input to be used as an active LOW clock enable ($\overline{\text{CE}}$) input. The pin assignment for the CP and $\overline{\text{CE}}$ inputs is arbitrary and can be reversed for layout convenience. The LOW-to-HIGH transition of input $\overline{\text{CE}}$ should only take place while CP HIGH for predictable operation. Either the CP or the $\overline{\text{CE}}$ should be HIGH before the LOW-to-HIGH transition of $\overline{\text{PL}}$ to prevent shifting the data when $\overline{\text{PL}}$ is activated.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from −40 °C to +85 °C and from −40 °C to +125 °C
- Asynchronous 8-bit parallel load
- Synchronous serial input
- Complies with JEDEC standard no. 7A
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

3. Applications

- Parallel-to-serial data conversion

4. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC165D-Q100 74HCT165D-Q100	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HC165PW-Q100 74HCT165PW-Q100	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HC165BQ-Q100 74HCT165BQ-Q100	–40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1

5. Functional diagram

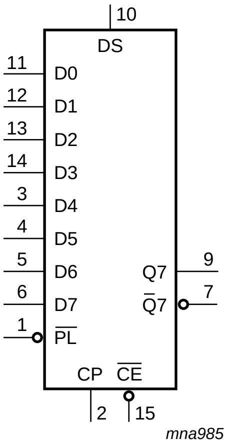


Fig 1. Logic symbol

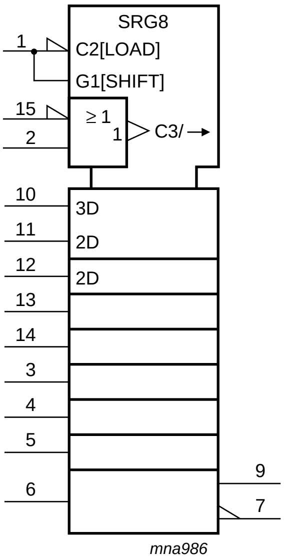


Fig 2. IEC logic symbol

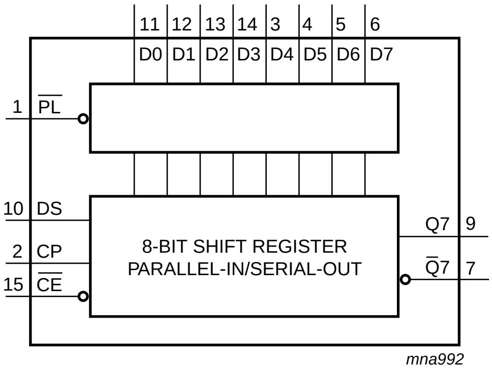


Fig 3. Functional diagram

6. Pinning information

6.1 Pinning

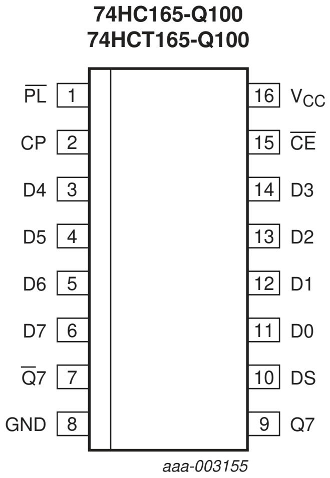
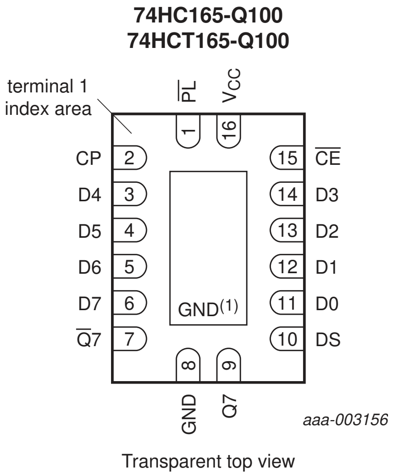


Fig 4. Pin configuration SO16 and TSSOP16



(1) This is not a supply pin. The substrate is attached to this pad using conductive die attach material. There is no electrical or mechanical requirement to solder this pad. However, if it is soldered, the solder land should remain floating or be connected to GND.

Fig 5. Pin configuration DHVQFN16

6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$\overline{PL}$	1	asynchronous parallel load input (active LOW)
CP	2	clock input (LOW-to-HIGH edge-triggered)
$\overline{Q7}$	7	complementary output from the last stage
GND	8	ground (0 V)
Q7	9	serial output from the last stage
DS	10	serial data input
D0 to D7	11, 12, 13, 14, 3, 4, 5, 6	parallel data inputs (also referred to as Dn)
$\overline{CE}$	15	clock enable input (active LOW)
V_{CC}	16	positive supply voltage

7. Functional description

Table 3. Function table[1]

Operating modes	Inputs					Qn registers		Outputs	
	$\overline{PL}$	$\overline{CE}$	CP	DS	D0 to D7	Q0	Q1 to Q6	Q7	$\overline{Q7}$
parallel load	L	X	X	X	L	L	L to L	L	H
	L	X	X	X	H	H	H to H	H	L
serial shift	H	L	↑	l	X	L	q0 to q5	q6	$\overline{q6}$
	H	L	↑	h	X	H	q0 to q5	q6	$\overline{q6}$
	H	↑	L	l	X	L	q0 to q5	q6	$\overline{q6}$
	H	↑	L	h	X	H	q0 to q5	q6	$\overline{q6}$
hold “do nothing”	H	H	X	X	X	q0	q1 to q6	q7	$\overline{q7}$
	H	X	H	X	X	q0	q1 to q6	q7	$\overline{q7}$

[1] H = HIGH voltage level;
h = HIGH voltage level one set-up time prior to the LOW-to-HIGH clock transition;
L = LOW voltage level;
l = LOW voltage level one set-up time prior to the LOW-to-HIGH clock transition;
q = state of the referenced output one set-up time prior to the LOW-to-HIGH clock transition;
X = don’t care;
↑ = LOW-to-HIGH clock transition.

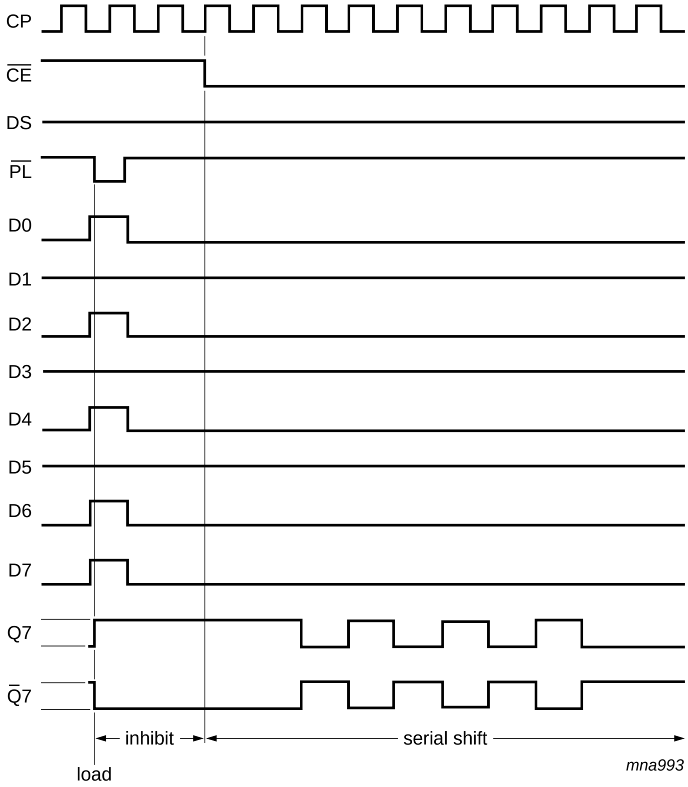


Fig 6. Timing diagram

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+7	V
I_{IK}	input clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V	[1]	-	±20	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	[1]	-	±20	mA
I_O	output current	-0.5 V $< V_O < V_{CC} + 0.5$ V		-	±25	mA
I_{CC}	supply current			-	50	mA
I_{GND}	ground current			–50	-	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	T_{amb} = –40 °C to +125 °C	[2]	-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 °C.
For TSSOP16 package: P_{tot} derates linearly with 5.5 mW/K above 60 °C.
For DHVQFN16 package: P_{tot} derates linearly with 4.5 mW/K above 60 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions
Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC165-Q100			74HCT165-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		–40	-	+125	–40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V_{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V_{CC} = 6.0 V	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 6. Static characteristics
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC165-Q100										
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V_{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V_{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V_{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V_{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}								
		I_O = –20 μA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_O = –20 μA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –20 μA; V_{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I_O = –4.0 mA; V_{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I_O = –5.2 mA; V_{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}								
		I_O = 20 μA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I_O = 5.2 mA; V_{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; V_{CC} = 6.0 V	-	-	±0.1	-	±1	-	±1	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 6.0 V	-	-	8.0	-	80	-	160	μA

Table 6. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
C_I	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT165-Q100										
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V								
		I_O = −20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = −4.0 mA	3.98	4.32	-	3.84	-	3.7	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V								
		I_O = 20 μA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 5.2 mA; V_{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; V_{CC} = 6.0 V	-	-	±0.1	-	±1	-	±1	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 6.0 V	-	-	8.0	-	80	-	160	μA
ΔI_{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1$ V; other inputs at V_{CC} or GND; V_{CC} = 4.5 V to 5.5 V								
		Dn and DS inputs	-	35	126	-	157.5	-	171.5	μA
		CP $\overline{CE}$, and $\overline{PL}$ inputs	-	65	234	-	292.5	-	318.5	μA
C_I	input capacitance		-	3.5	-	-	-	-	-	pF

11. Dynamic characteristics

Table 7. Dynamic characteristics

GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit, see Figure 12

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC165-Q100										
t_{pd}	propagation delay	CP or $\overline{CE}$ to Q7, $\overline{Q7}$; see Figure 7 [1]								
		V_{CC} = 2.0 V	-	52	165	-	205	-	250	ns
		V_{CC} = 4.5 V	-	19	33	-	41	-	50	ns
		V_{CC} = 6.0 V	-	15	28	-	35	-	43	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	16	-	-	-	-	-	ns
		$\overline{PL}$ to Q7, $\overline{Q7}$; see Figure 8								
		V_{CC} = 2.0 V	-	50	165	-	205	-	250	ns
		V_{CC} = 4.5 V	-	18	33	-	41	-	50	ns
		V_{CC} = 6.0 V	-	14	28	-	35	-	43	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	15	-	-	-	-	-	ns
		D7 to Q7, $\overline{Q7}$; see Figure 9								
		V_{CC} = 2.0 V	-	36	120	-	150	-	180	ns
		V_{CC} = 4.5 V	-	13	24	-	30	-	36	ns
		V_{CC} = 6.0 V	-	10	20	-	26	-	31	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	11	-	-	-	-	-	ns
t_t	transition time	Q7, $\overline{Q7}$ output; see Figure 7 [2]								
		V_{CC} = 2.0 V	-	19	75	-	95	-	110	ns
		V_{CC} = 4.5 V	-	7	15	-	19	-	22	ns
		V_{CC} = 6.0 V	-	6	13	-	16	-	19	ns
t_W	pulse width	CP input HIGH or LOW; see Figure 7								
		V_{CC} = 2.0 V	80	17	-	100	-	120	-	ns
		V_{CC} = 4.5 V	16	6	-	20	-	24	-	ns
		V_{CC} = 6.0 V	14	5	-	17	-	20	-	ns
		$\overline{PL}$ input LOW; see Figure 8								
		V_{CC} = 2.0 V	80	14	-	100	-	120	-	ns
		V_{CC} = 4.5 V	16	5	-	20	-	24	-	ns
		V_{CC} = 6.0 V	14	4	-	17	-	20	-	ns
t_{rec}	recovery time	$\overline{PL}$ to CP, $\overline{CE}$; see Figure 8								
		V_{CC} = 2.0 V	100	22	-	125	-	150	-	ns
		V_{CC} = 4.5 V	20	8	-	25	-	30	-	ns
		V_{CC} = 6.0 V	17	6	-	21	-	26	-	ns

Table 7. Dynamic characteristics *…continued*

GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit, see Figure 12

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_{su}	set-up time	DS to CP, $\overline{CE}$; see Figure 10								
		V_{CC} = 2.0 V	80	11	-	100	-	120	-	ns
		V_{CC} = 4.5 V	16	4	-	20	-	24	-	ns
		V_{CC} = 6.0 V	14	3	-	17	-	20	-	ns
		$\overline{CE}$ to CP and CP to $\overline{CE}$; see Figure 10								
		V_{CC} = 2.0 V	80	17	-	100	-	120	-	ns
		V_{CC} = 4.5 V	16	6	-	20	-	24	-	ns
		V_{CC} = 6.0 V	14	5	-	17	-	20	-	ns
		Dn to $\overline{PL}$; see Figure 11								
		V_{CC} = 2.0 V	80	22	-	100	-	120	-	ns
		V_{CC} = 4.5 V	16	8	-	20	-	24	-	ns
		V_{CC} = 6.0 V	14	6	-	17	-	20	-	ns
t_h	hold time	DS to CP, $\overline{CE}$ and Dn to $\overline{PL}$; see Figure 10								
		V_{CC} = 2.0 V	5	6	-	5	-	5	-	ns
		V_{CC} = 4.5 V	5	2	-	5	-	5	-	ns
		V_{CC} = 6.0 V	5	2	-	5	-	5	-	ns
		$\overline{CE}$ to CP and CP to $\overline{CE}$; see Figure 10								
		V_{CC} = 2.0 V	5	−17	-	5	-	5	-	ns
		V_{CC} = 4.5 V	5	−6	-	5	-	5	-	ns
		V_{CC} = 6.0 V	5	−5	-	5	-	5	-	ns
f_{max}	maximum frequency	CP input; see Figure 7								
		V_{CC} = 2.0 V	6	17	-	5	-	4	-	MHz
		V_{CC} = 4.5 V	30	51	-	24	-	20	-	MHz
		V_{CC} = 6.0 V	35	61	-	28	-	24	-	MHz
		V_{CC} = 5.0 V; C_L = 15 pF	-	56	-	-	-	-	-	MHz
C_{PD}	power dissipation capacitance	per package; V_I = GND to V_{CC} [3]	-	35	-	-	-	-	-	pF

Table 7. Dynamic characteristics *...continued*

GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit, see Figure 12

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HCT165-Q100										
t_{pd}	propagation delay	$\overline{\text{CE}}$, CP to Q7, $\overline{\text{Q7}}$; see Figure 7 [1]								
		V_{CC} = 4.5 V	-	17	34	-	43	-	51	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	14	-	-	-	-	-	ns
		$\overline{\text{PL}}$ to Q7, $\overline{\text{Q7}}$; see Figure 8								
		V_{CC} = 4.5 V	-	20	40	-	50	-	60	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	17	-	-	-	-	-	ns
		D7 to Q7, $\overline{\text{Q7}}$; see Figure 9								
		V_{CC} = 4.5 V	-	14	28	-	35	-	42	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	11	-	-	-	-	-	ns
t_t	transition time	Q7, $\overline{\text{Q7}}$ output; see Figure 7 [2]								
		V_{CC} = 4.5 V	-	7	15	-	19	-	22	ns
t_W	pulse width	CP input; see Figure 7								
		V_{CC} = 4.5 V	16	6	-	20	-	24	-	ns
		$\overline{\text{PL}}$ input; see Figure 8								
		V_{CC} = 4.5 V	20	9	-	25	-	30	-	ns
t_{rec}	recovery time	$\overline{\text{PL}}$ to CP, $\overline{\text{CE}}$; see Figure 8								
		V_{CC} = 4.5 V	20	8	-	25	-	30	-	ns
t_{su}	set-up time	DS to CP, $\overline{\text{CE}}$; see Figure 10								
		V_{CC} = 4.5 V	20	2	-	25	-	30	-	ns
		$\overline{\text{CE}}$ to CP and CP to $\overline{\text{CE}}$; see Figure 10								
		V_{CC} = 4.5 V	20	7	-	25	-	30	-	ns
		Dn to $\overline{\text{PL}}$; see Figure 11								
		V_{CC} = 4.5 V	20	10	-	25	-	30	-	ns
t_h	hold time	DS to CP, $\overline{\text{CE}}$ and Dn to $\overline{\text{PL}}$; see Figure 10								
		V_{CC} = 4.5 V	7	−1	-	9	-	11	-	ns
		$\overline{\text{CE}}$ to CP and CP to $\overline{\text{CE}}$; see Figure 10								
		V_{CC} = 4.5 V	0	−7	-	0	-	0	-	ns
f_{max}	maximum frequency	CP input; see Figure 7								
		V_{CC} = 4.5 V	26	44	-	21	-	17	-	MHz
		V_{CC} = 5.0 V; C_L = 15 pF	-	48	-	-	-	-	-	MHz

Table 7. Dynamic characteristics *…continued*

GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit, see Figure 12

Symbol	Parameter	Conditions		25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
C_{PD}	power dissipation capacitance	per package; V_I = GND to V_{CC} − 1.5 V	[3]	-	35	-	-	-	-	-	pF

[1] t_{pd} is the same as t_{PHL} and t_{PLH}.

[2] t_t is the same as t_{THL} and t_{TLH}.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

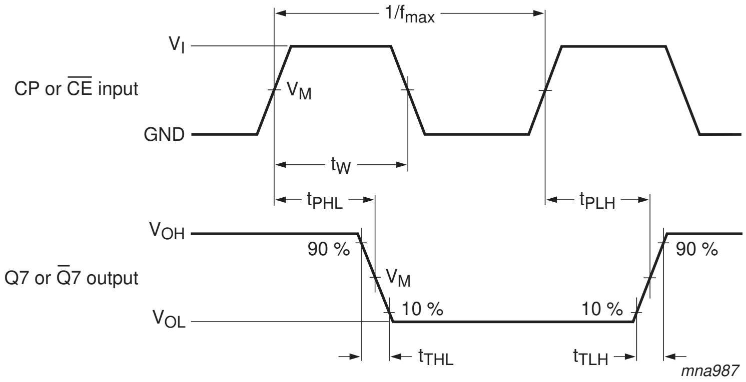
f_o = output frequency in MHz;

$\Sigma (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V.

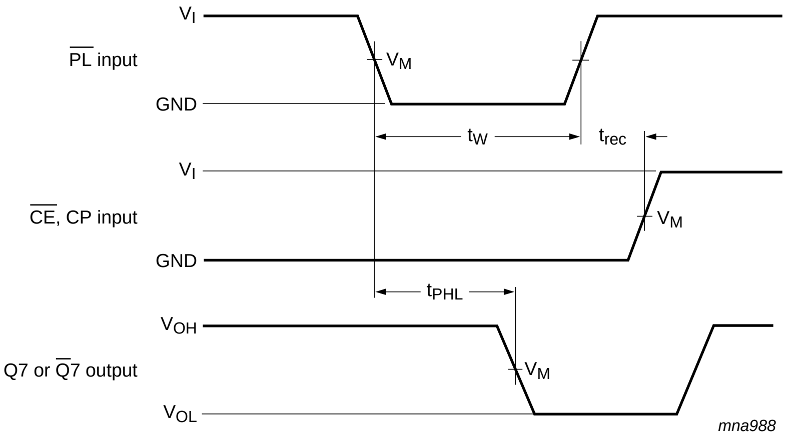
12. Waveforms



Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

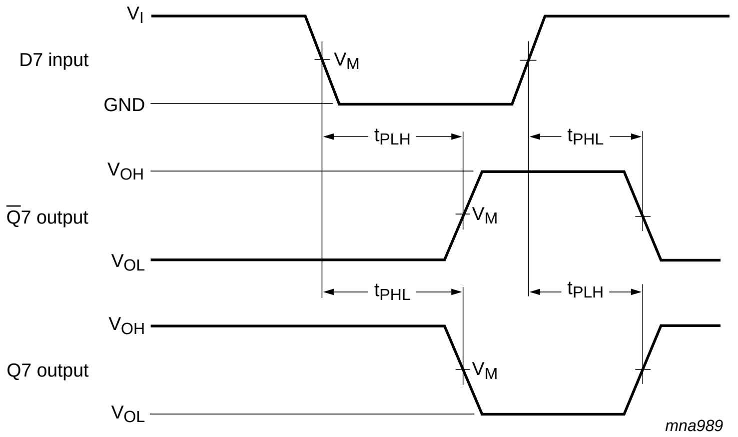
Fig 7. Clock (CP) or clock enable ($\overline{CE}$) to output (Q7 or $\overline{Q7}$) propagation delays, clock pulse width, maximum clock frequency and output transition times



Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

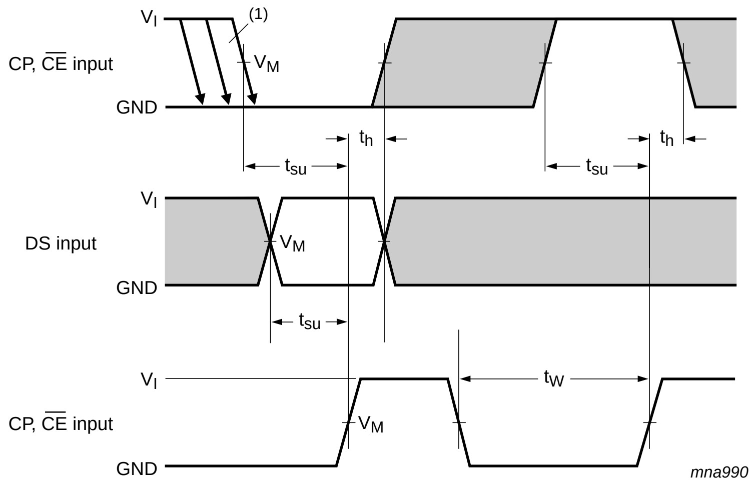
Fig 8. Parallel load ($\overline{PL}$) pulse width, parallel load to output (Q7 or $\overline{Q7}$) propagation delays, parallel load to clock (CP) and clock enable ($\overline{CE}$) recovery time



Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 9. Data input (D7) to output (Q7 or $\overline{Q7}$) propagation delays when $\overline{PL}$ is LOW



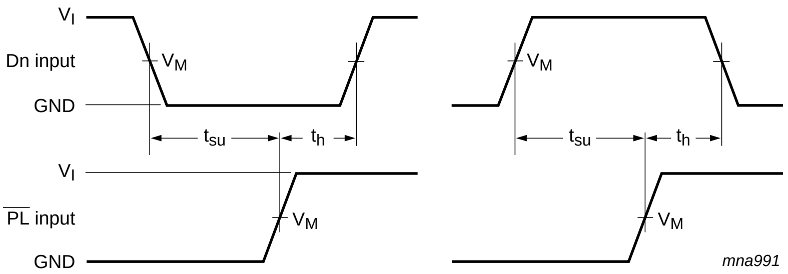
The shaded areas indicate when the input is permitted to change for predictable output performance

Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

(1) $\overline{CE}$ may change only from HIGH-to-LOW while CP is LOW, see Section 1.

Fig 10. Waveforms showing set-up and hold times



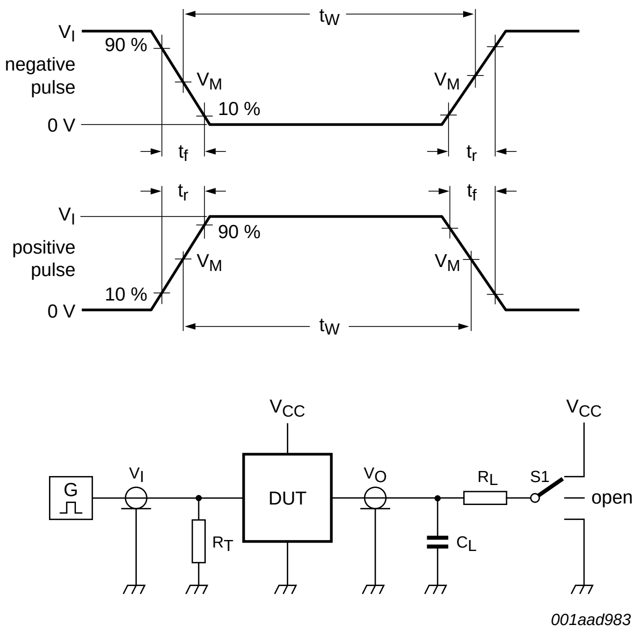
Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 11. The set-up and hold times from the data inputs (Dn) to the parallel load input ($\overline{PL}$)

Table 8. Measurement points

Type	Input		Output
	V_I	V_M	V_M
74HC165-Q100	V_{CC}	$0.5V_{CC}$	$0.5V_{CC}$
74HCT165-Q100	3 V	1.3 V	1.3 V



Test data is given in Table 9.

Definitions for test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch

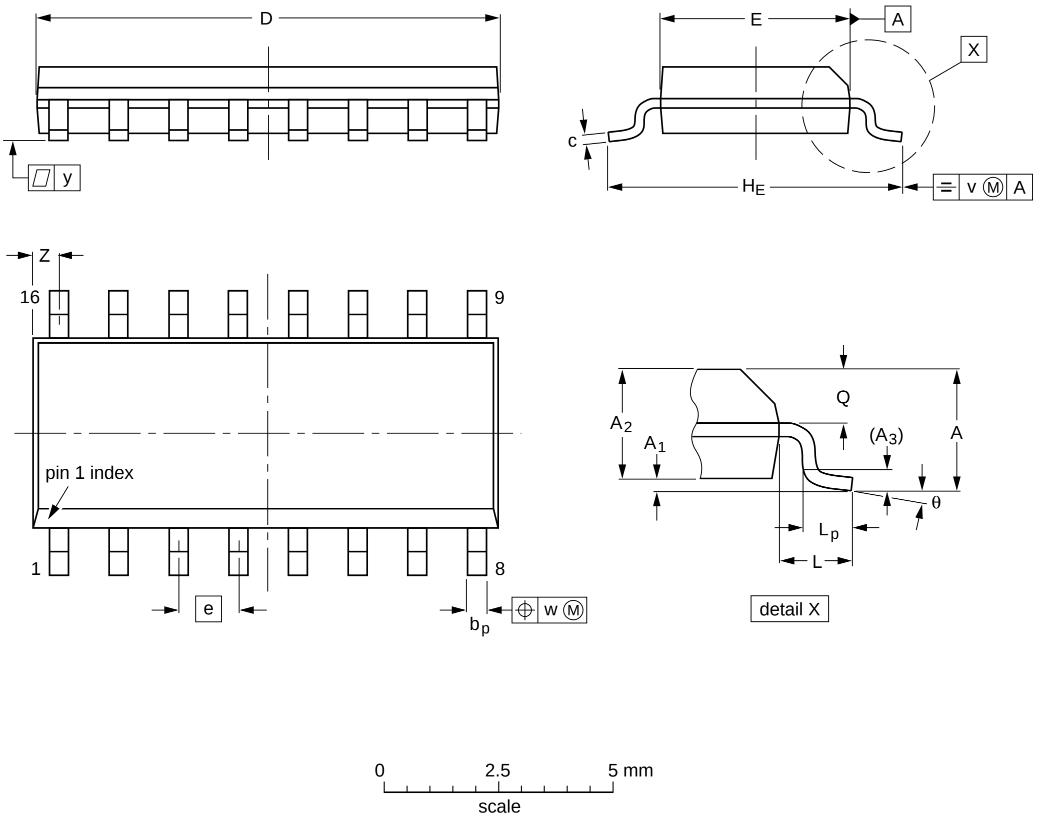
Fig 12. Test circuit for measuring switching times

Table 9. Test data

Type	Input		Load		S1 position
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}
74HC165-Q100	V_{CC}	6 ns	15 pF, 50 pF	1 kΩ	open
74HCT165-Q100	3 V	6 ns	15 pF, 50 pF	1 kΩ	open

13. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm **SOT109-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D(1)	E(1)	e	H_E	L	L_p	Q	v	w	y	Z(1)	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

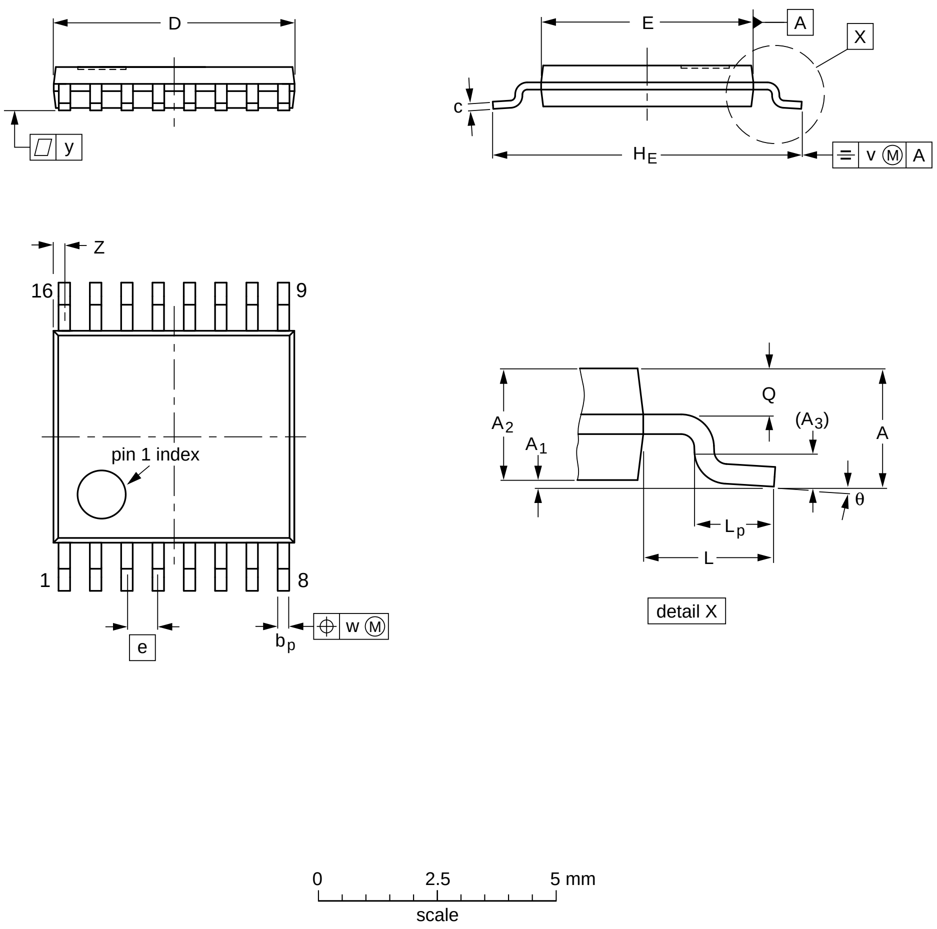
Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT109-1	076E07	MS-012				~~99-12-27~~ 03-02-19

Fig 13. Package outline SOT109-1 (SO16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm **SOT403-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

Notes

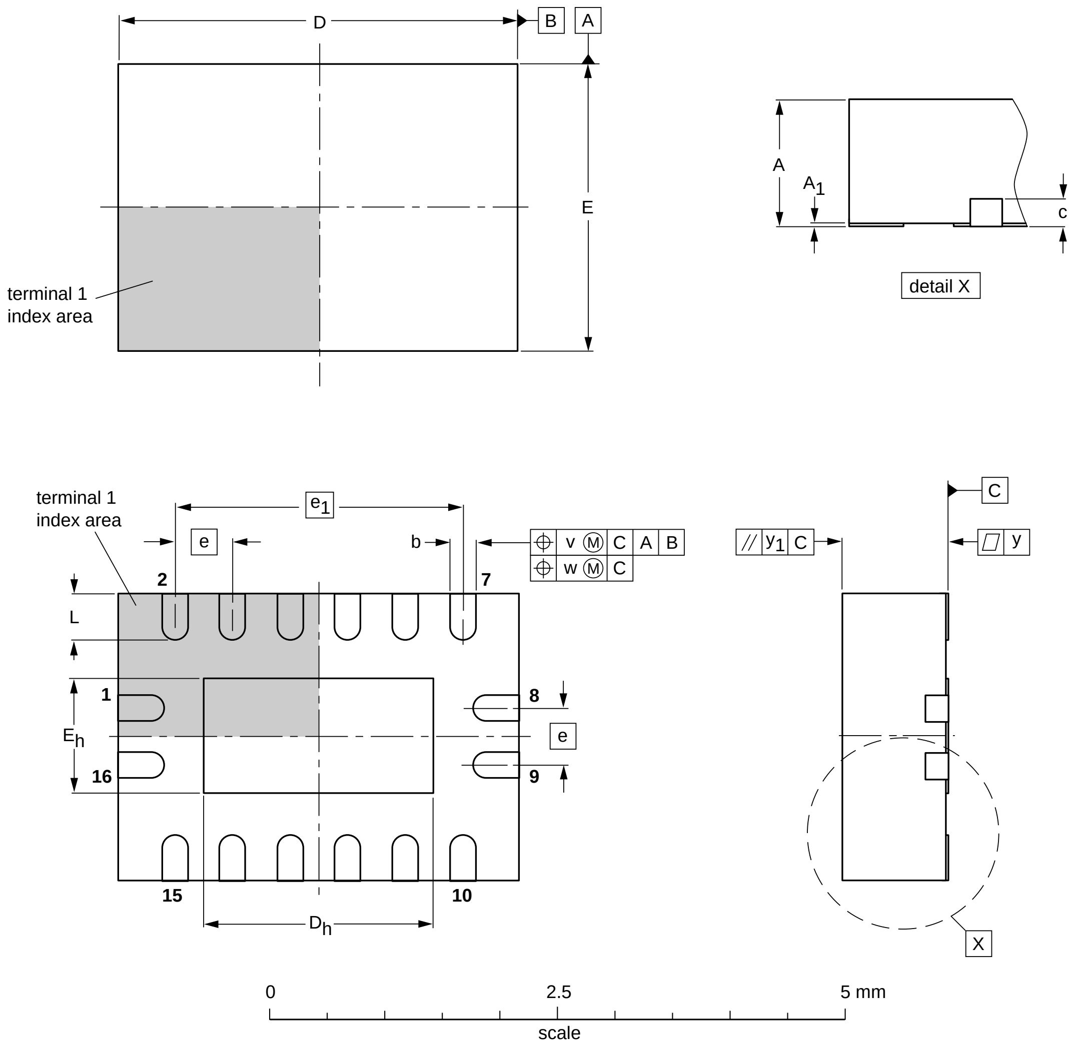
1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT403-1		MO-153				~~99-12-27~~ 03-02-18

Fig 14. Package outline SOT403-1 (TSSOP16)

DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm

SOT763-1



DIMENSIONS (mm are the original dimensions)

UNIT	A(1) max.	A_1	b	c	D(1)	D_h	E(1)	E_h	e	e_1	L	v	w	y	y_1
mm	1	0.05 0.00	0.30 0.18	0.2	3.6 3.4	2.15 1.85	2.6 2.4	1.15 0.85	0.5	2.5	0.5 0.3	0.1	0.05	0.05	0.1

Note

1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT763-1	- - -	MO-241	- - -			~~02-10-17~~ 03-01-27

Fig 15. Package outline SOT763-1 (DHVQFN16)

14. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic
MIL	Military

15. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT165_Q100 v.1	20120717	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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18. Contents

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